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**NATIONAL STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

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**Test method for measuring the Al fraction in AlGaAs on GaAs
substrates by high resolution X-ray diffraction**

高分辨率X射线衍射测量GaAs衬底生长的AlGaAs中Al成分的试验方法

(English Translation)

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What this standard covers

This standard specifies test methods AlGaAs, Al content in the epitaxial layer by high resolution X -ray diffraction measurements on a GaAs substrate. This method is applicable to the determination of the direction of growth of the Al content in AlGaAs epitaxial layer in the GaAs substrate is undoped. When using this method to measure the Al content, AlGaAs epitaxial layer thickness should be greater than 300 nm.

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